



STP75NF75L STB75NF75L STB75NF75L-1

N-CHANNEL 75V - 0.009 Ω - 75A D²PAK/I²PAK/TO-220
STripFET™ II POWER MOSFET

| TYPE | V _{DSS} | R _{DS(on)} | I _D |
|---------------|------------------|---------------------|----------------|
| STB75NF75L/-1 | 75 V | <0.011 Ω | 75 A |
| STP75NF75L | 75 V | <0.011 Ω | 75 A |

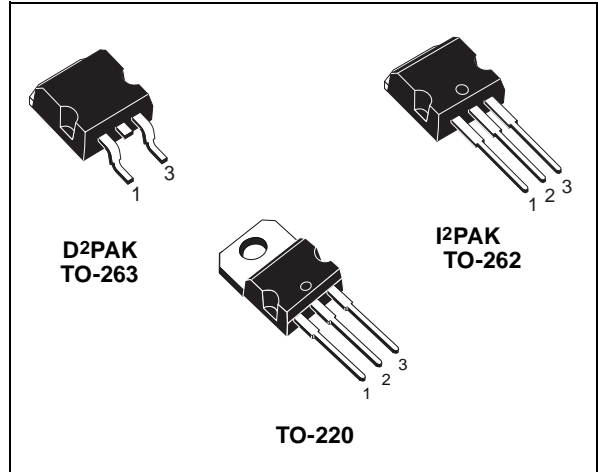
- TYPICAL R_{DS(on)} = 0.009Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- LOW THRESHOLD DRIVE

DESCRIPTION

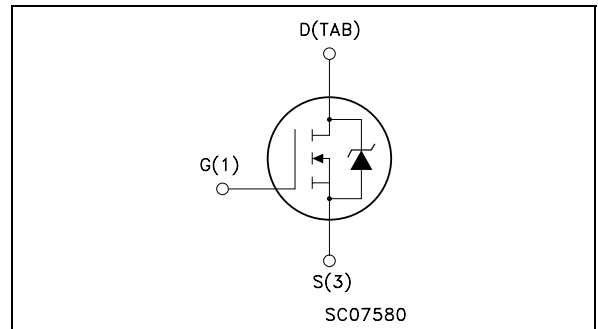
This MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency, high-frequency isolated DC-DC converters for Telecom and Computer applications. It is also intended for any applications with low gate drive requirements.

APPLICATIONS

- SOLENOID AND RELAY DRIVERS
- DC MOTOR CONTROL
- DC-DC CONVERTERS
- AUTOMOTIVE ENVIRONMENT



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|---------------------|--|------------|------|
| V _{DS} | Drain-source Voltage (V _{GS} = 0) | 75 | V |
| V _{DGR} | Drain-gate Voltage (R _{GS} = 20 kΩ) | 75 | V |
| V _{GS} | Gate- source Voltage | ± 15 | V |
| I _{D(●)} | Drain Current (continuous) at T _C = 25°C | 75 | A |
| I _D | Drain Current (continuous) at T _C = 100°C | 70 | A |
| I _{DM(●●)} | Drain Current (pulsed) | 300 | A |
| P _{tot} | Total Dissipation at T _C = 25°C | 300 | W |
| | Derating Factor | 2 | W/°C |
| dv/dt (1) | Peak Diode Recovery voltage slope | 20 | V/ns |
| E _{AS} (2) | Single Pulse Avalanche Energy | 680 | mJ |
| T _{stg} | Storage Temperature | -55 to 175 | °C |
| T _j | Max. Operating Junction Temperature | | |

(●) Current limited by package

(●●) Pulse width limited by safe operating area.

(1) I_{SD} ≤ 75A, di/dt ≤ 500A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}.

(2) Starting T_j = 25 °C, I_D = 37.5A, V_{DD} = 30V

STB75NF75L/-1 STP75NF75L**THERMAL DATA**

| | | | | |
|----------------|--|-----|------|------|
| Rthj-case | Thermal Resistance Junction-case | Max | 0.5 | °C/W |
| Rthj-amb | Thermal Resistance Junction-ambient | Max | 62.5 | °C/W |
| T _l | Maximum Lead Temperature For Soldering Purpose | Typ | 300 | °C |

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|----------------------|---|---|------|------|---------|----------|
| V _{(BR)DSS} | Drain-source Breakdown Voltage | I _D = 250 μA V _{GS} = 0 | 75 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current (V _{GS} = 0) | V _{DS} = Max Rating V _{DS} = Max Rating T _C = 125°C | | | 1 10 | μA μA |
| I _{GSS} | Gate-body Leakage Current (V _{DS} = 0) | V _{GS} = ± 15 V | | | ±100 | nA |

ON (*)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------|-----------------------------------|---|------|----------------|----------------|--------|
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} I _D = 250 μA | 1 | | 2.5 | V |
| R _{DS(on)} | Static Drain-source On Resistance | V _{GS} = 10 V I _D = 37.5 A V _{GS} = 5 V I _D = 37.5 A | | 0.009 0.010 | 0.011 0.013 | Ω Ω |

DYNAMIC

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--|---|---|------|--------------------|------|----------------|
| g _{fs} (*) | Forward Transconductance | V _{DS} = 15 V I _D = 37.5 A | | 120 | | S |
| C _{iss} C _{oss} C _{rss} | Input Capacitance Output Capacitance Reverse Transfer Capacitance | V _{DS} = 25V, f = 1 MHz, V _{GS} = 0 | | 4300 660 205 | | pF pF pF |

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-------------------------------|--|---|------|----------------|------|----------------|
| $t_{d(on)}$ t_r | Turn-on Delay Time Rise Time | $V_{DD} = 40\text{ V}$ $I_D = 37.5\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$ (Resistive Load, Figure 3) | | 35 150 | | ns ns |
| Q_g Q_{gs} Q_{gd} | Total Gate Charge Gate-Source Charge Gate-Drain Charge | $V_{DD} = 60\text{ V}$ $I_D = 75\text{ A}$ $V_{GS} = 5\text{ V}$ | | 75 18 31 | 90 | nC nC nC |

SWITCHING OFF

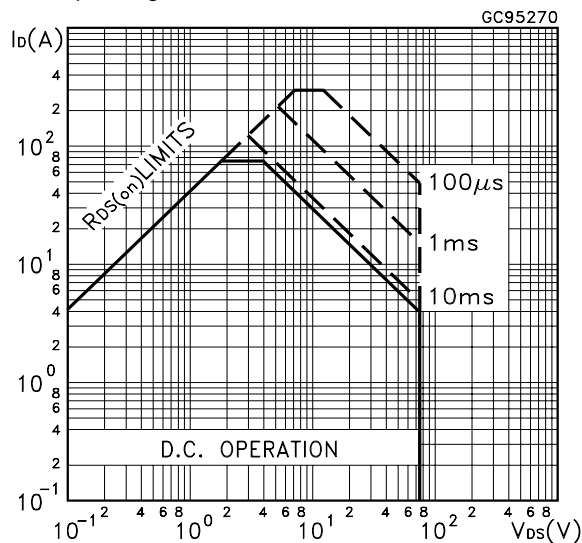
| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-----------------------|----------------------------------|---|------|-----------|------|----------|
| $t_{d(off)}$ t_f | Turn-off Delay Time Fall Time | $V_{DD} = 40\text{ V}$ $I_D = 37.5\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 4.5\text{ V}$ (Resistive Load, Figure 3) | | 110 60 | | ns ns |

SOURCE DRAIN DIODE

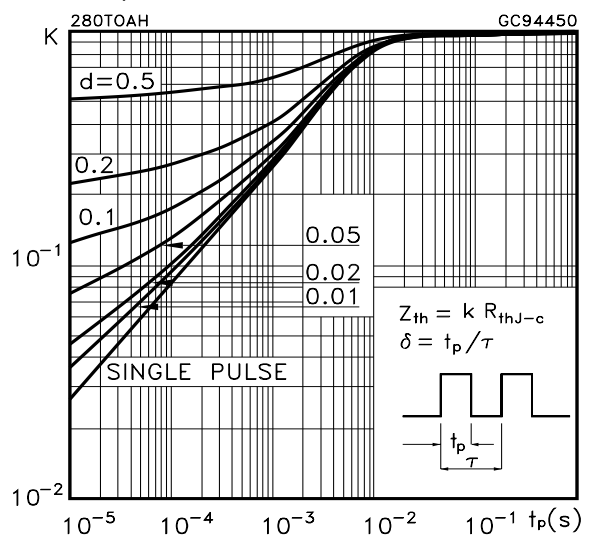
| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-----------------------------------|--|---|------|-------------------|-----------|---------------|
| I_{SD} $I_{SDM}^{(*)}$ | Source-drain Current Source-drain Current (pulsed) | | | | 75 300 | A A |
| $V_{SD}^{(*)}$ | Forward On Voltage | $I_{SD} = 75\text{ A}$ $V_{GS} = 0$ | | | 1.3 | V |
| t_{rr} Q_{rr} I_{RRM} | Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current | $I_{SD} = 75\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 20\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5) | | 100 380 7.5 | | ns nC A |

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
 (•) Pulse width limited by safe operating area.

Safe Operating Area

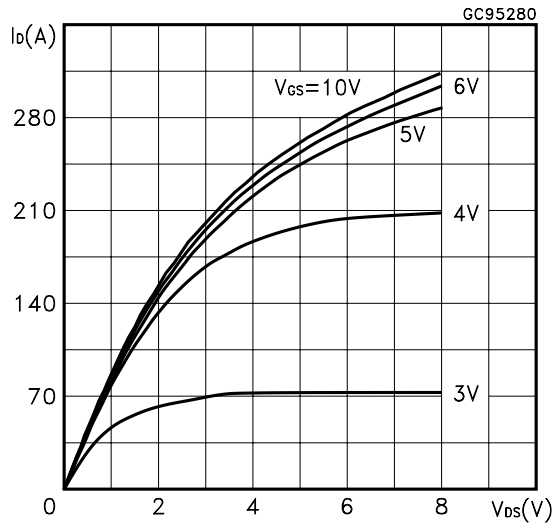


Thermal Impedance

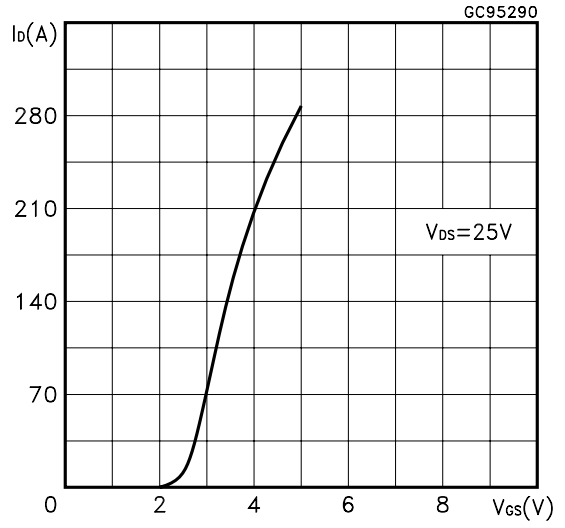


STB75NF75L/-1 STP75NF75L

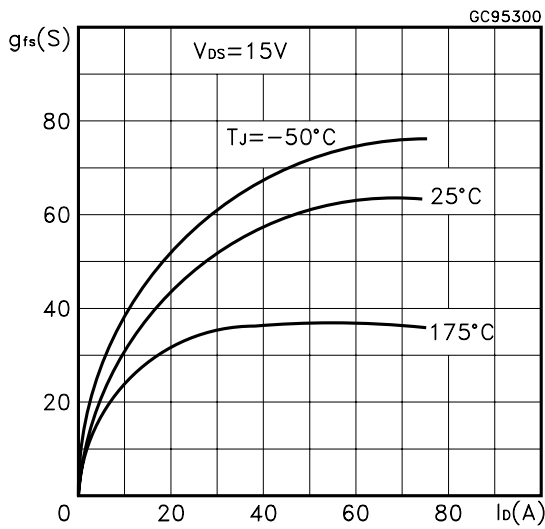
Output Characteristics



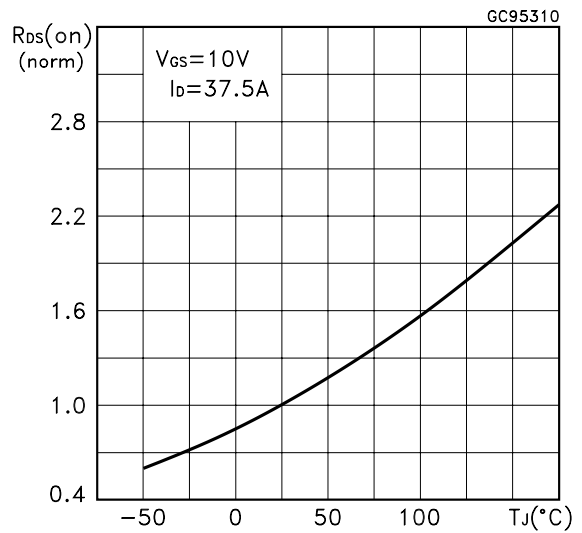
Transfer Characteristics



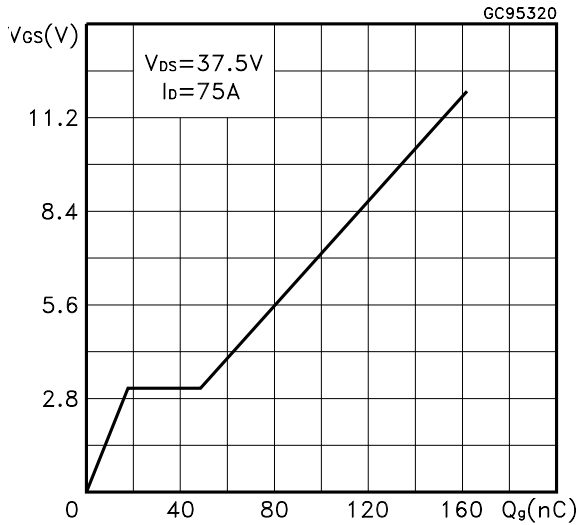
Transconductance



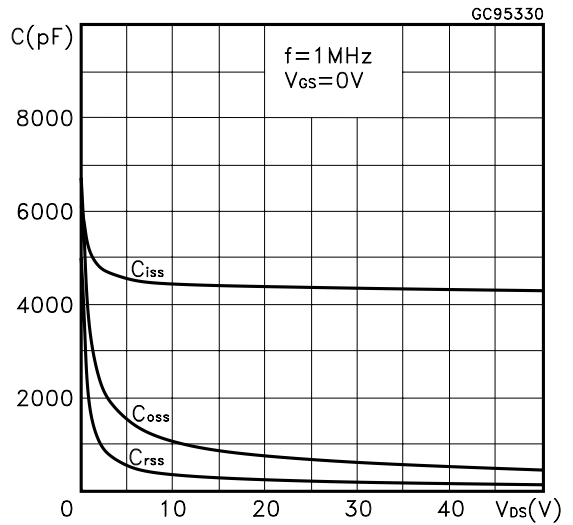
Static Drain-source On Resistance



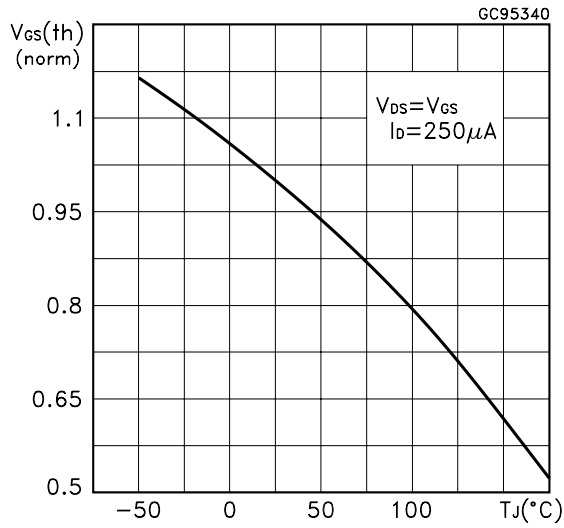
Gate Charge vs Gate-source Voltage



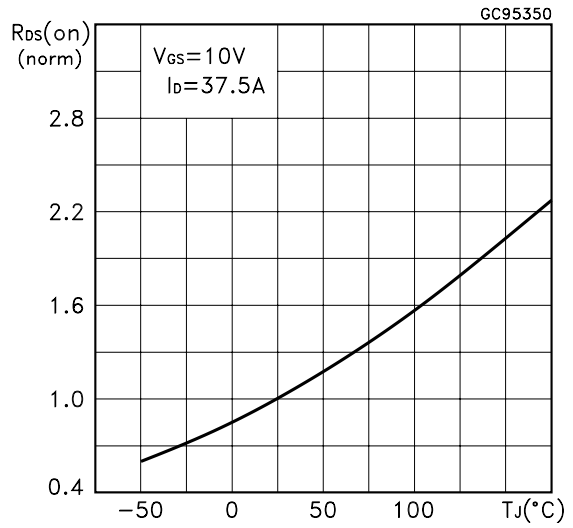
Capacitance Variations



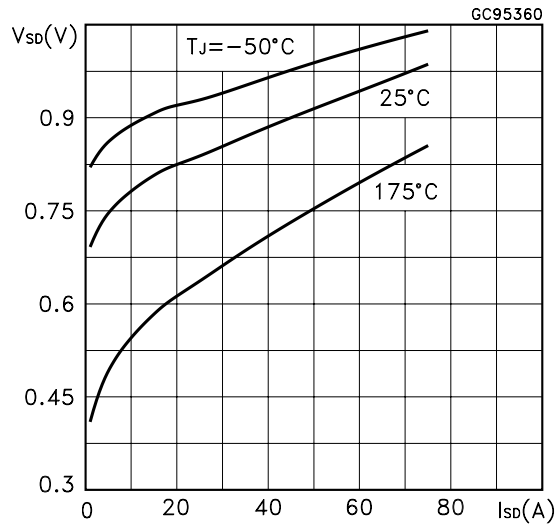
Normalized Gate Threshold Voltage vs Temperature



Normalized on Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized Breakdown Voltage vs Temperature.

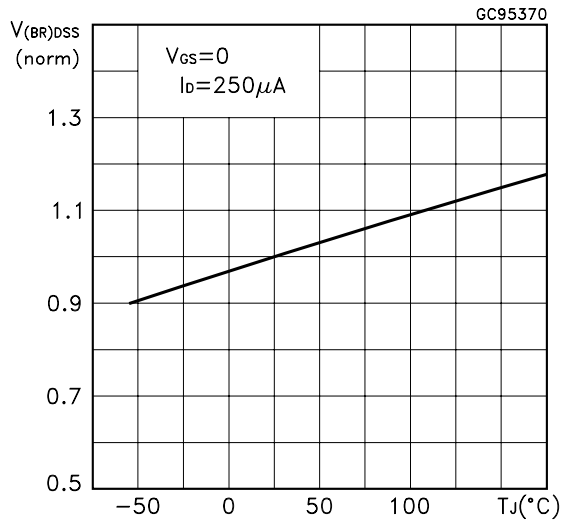


Fig. 1: Unclamped Inductive Load Test Circuit



Fig. 2: Unclamped Inductive Waveform



Fig. 3: Switching Times Test Circuits For Resistive Load



Fig. 4: Gate Charge test Circuit

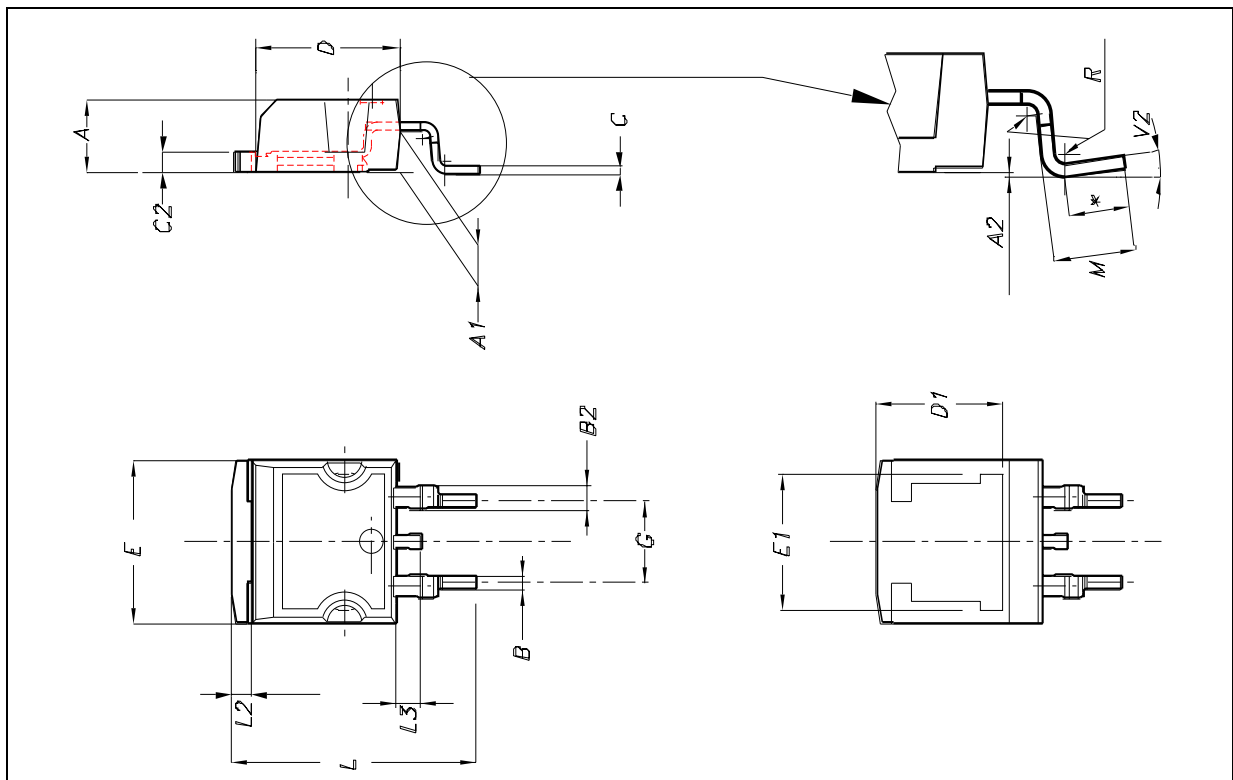


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



D²PAK MECHANICAL DATA

| DIM. | mm. | | | inch. | | |
|------|------|------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | TYP. |
| A | 4.4 | | 4.6 | 0.173 | | 0.181 |
| A1 | 2.49 | | 2.69 | 0.098 | | 0.106 |
| A2 | 0.03 | | 0.23 | 0.001 | | 0.009 |
| B | 0.7 | | 0.93 | 0.028 | | 0.037 |
| B2 | 1.14 | | 1.7 | 0.045 | | 0.067 |
| C | 0.45 | | 0.6 | 0.018 | | 0.024 |
| C2 | 1.21 | | 1.36 | 0.048 | | 0.054 |
| D | 8.95 | | 9.35 | 0.352 | | 0.368 |
| D1 | | 8 | | | 0.315 | |
| E | 10 | | 10.4 | 0.394 | | 0.409 |
| E1 | 8.5 | | | | 0.334 | |
| G | 4.88 | | 5.28 | 0.192 | | 0.208 |
| L | 15 | | 15.85 | 0.591 | | 0.624 |
| L2 | 1.27 | | 1.4 | 0.050 | | 0.055 |
| L3 | 1.4 | | 1.75 | 0.055 | | 0.069 |
| M | 2.4 | | 3.2 | 0.094 | | 0.126 |
| R | | 0.4 | | | 0.016 | |
| V2 | 0° | | 8° | 0° | | 8° |



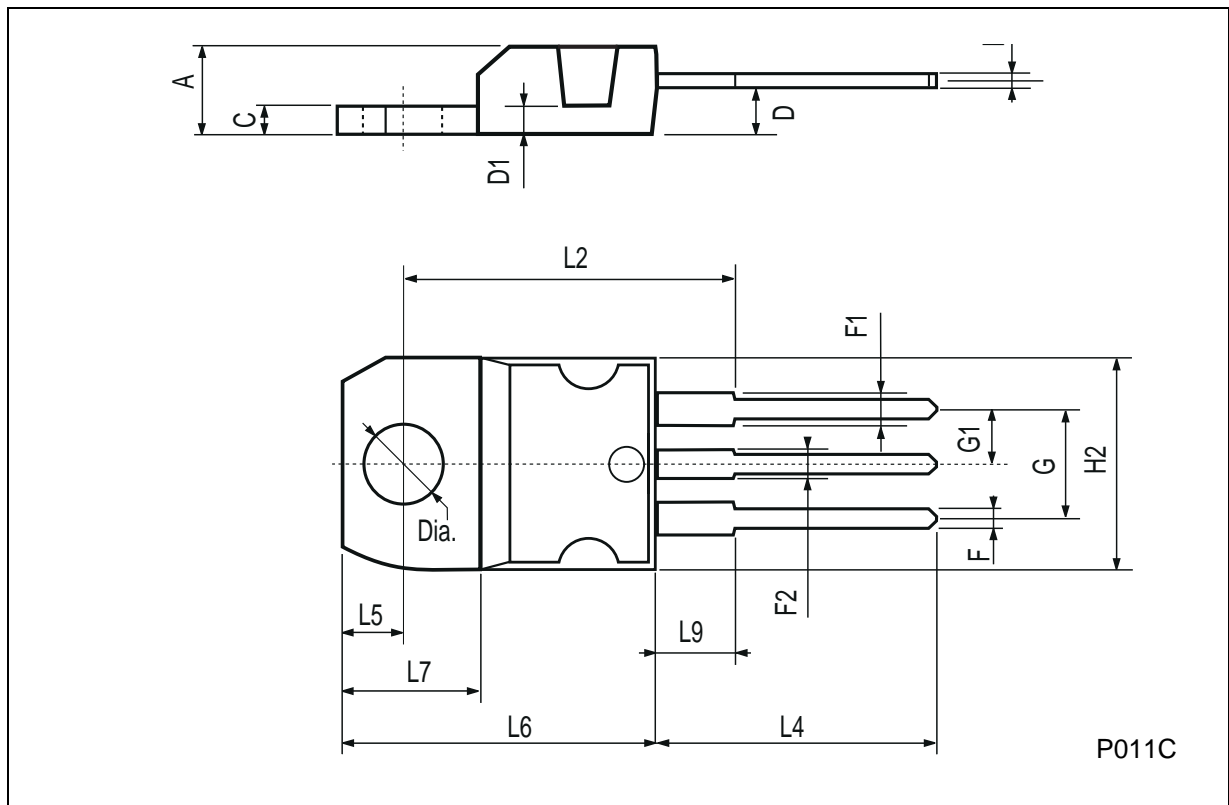
TO-262 (I²PAK) MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|------|------|------|-------|------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 4.4 | | 4.6 | 0.173 | | 0.181 |
| A1 | 2.49 | | 2.69 | 0.098 | | 0.106 |
| B | 0.7 | | 0.93 | 0.027 | | 0.036 |
| B2 | 1.14 | | 1.7 | 0.044 | | 0.067 |
| C | 0.45 | | 0.6 | 0.017 | | 0.023 |
| C2 | 1.23 | | 1.36 | 0.048 | | 0.053 |
| D | 8.95 | | 9.35 | 0.352 | | 0.368 |
| e | 2.4 | | 2.7 | 0.094 | | 0.106 |
| E | 10 | | 10.4 | 0.393 | | 0.409 |
| L | 13.1 | | 13.6 | 0.515 | | 0.531 |
| L1 | 3.48 | | 3.78 | 0.137 | | 0.149 |
| L2 | 1.27 | | 1.4 | 0.050 | | 0.055 |

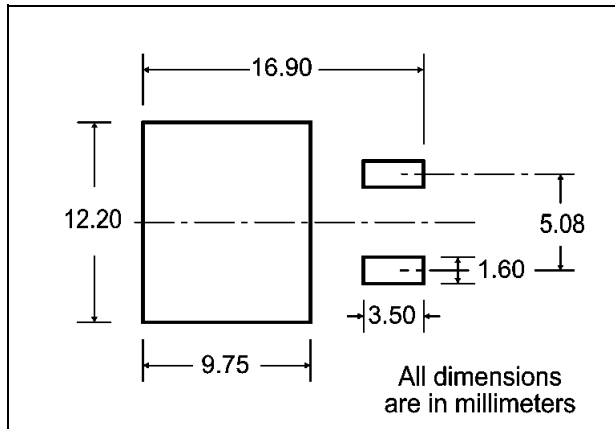


TO-220 MECHANICAL DATA

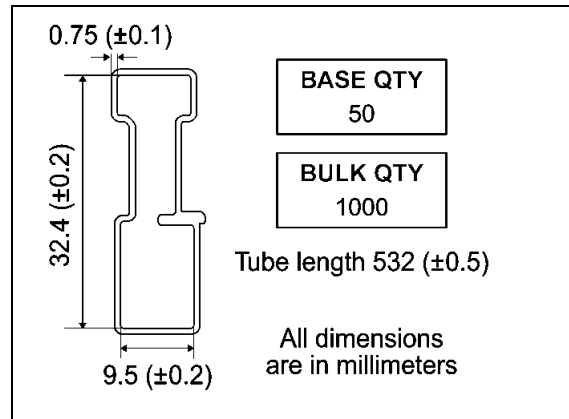
| DIM. | mm | | | inch | | |
|------|-------|------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 4.40 | | 4.60 | 0.173 | | 0.181 |
| C | 1.23 | | 1.32 | 0.048 | | 0.051 |
| D | 2.40 | | 2.72 | 0.094 | | 0.107 |
| D1 | | 1.27 | | | 0.050 | |
| E | 0.49 | | 0.70 | 0.019 | | 0.027 |
| F | 0.61 | | 0.88 | 0.024 | | 0.034 |
| F1 | 1.14 | | 1.70 | 0.044 | | 0.067 |
| F2 | 1.14 | | 1.70 | 0.044 | | 0.067 |
| G | 4.95 | | 5.15 | 0.194 | | 0.203 |
| G1 | 2.4 | | 2.7 | 0.094 | | 0.106 |
| H2 | 10.0 | | 10.40 | 0.393 | | 0.409 |
| L2 | | 16.4 | | | 0.645 | |
| L4 | 13.0 | | 14.0 | 0.511 | | 0.551 |
| L5 | 2.65 | | 2.95 | 0.104 | | 0.116 |
| L6 | 15.25 | | 15.75 | 0.600 | | 0.620 |
| L7 | 6.2 | | 6.6 | 0.244 | | 0.260 |
| L9 | 3.5 | | 3.93 | 0.137 | | 0.154 |
| DIA. | 3.75 | | 3.85 | 0.147 | | 0.151 |



D2PAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

G measured at hub

REEL MECHANICAL DATA

| DIM. | mm | | inch | |
|------|------|------|-------|--------|
| | MIN. | MAX. | MIN. | MAX. |
| A | | 330 | | 12.992 |
| B | 1.5 | | 0.059 | |
| C | 12.8 | 13.2 | 0.504 | 0.520 |
| D | 20.2 | | 0.795 | |
| G | 24.4 | 26.4 | 0.960 | 1.039 |
| N | 100 | | 3.937 | |
| T | | 30.4 | | 1.197 |

| | |
|-----------------|-----------------|
| BASE QTY | BULK QTY |
| 1000 | 1000 |

TAPE MECHANICAL DATA

| DIM. | mm | | inch | |
|------|------|------|--------|--------|
| | MIN. | MAX. | MIN. | MAX. |
| A0 | 10.5 | 10.7 | 0.413 | 0.421 |
| B0 | 15.7 | 15.9 | 0.618 | 0.626 |
| D | 1.5 | 1.6 | 0.059 | 0.063 |
| D1 | 1.59 | 1.61 | 0.062 | 0.063 |
| E | 1.65 | 1.85 | 0.065 | 0.073 |
| F | 11.4 | 11.6 | 0.449 | 0.456 |
| K0 | 4.8 | 5.0 | 0.189 | 0.197 |
| P0 | 3.9 | 4.1 | 0.153 | 0.161 |
| P1 | 11.9 | 12.1 | 0.468 | 0.476 |
| P2 | 1.9 | 2.1 | 0.075 | 0.082 |
| R | 50 | | 1.574 | |
| T | 0.25 | 0.35 | 0.0098 | 0.0137 |
| W | 23.7 | 24.3 | 0.933 | 0.956 |

10 pitches cumulative tolerance on tape +/- 0.2 mm

Center line of cavity

User Direction of Feed

FEED DIRECTION

Bending radius R min.

* on sales type

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